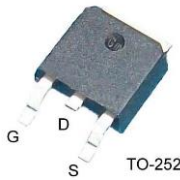
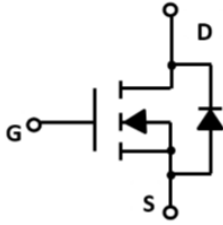


<p>Features</p> <ul style="list-style-type: none"> • 30V, 150A • $R_{DS(ON)} = 3.0m\Omega$ (Max.) @ $V_{GS} = 10V, I_D = 30A$ • Advanced Trench Technology • Provide Excellent $R_{DS(ON)}$ and Low Gate Charge 	<p>Application</p> <ul style="list-style-type: none"> • PWM Application • Load Switch • Power Management
<p>Package</p> <div style="display: flex; justify-content: space-around; align-items: center;">   </div> <p style="text-align: center;">TO-252 SFD160N03AT</p>	

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise specified

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	160
		$T_C = 100^\circ C$	150
I_{DM}	Pulsed Drain Current ^{note1}	400	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	650	mJ
P_D	Power Dissipation	$T_C = 25^\circ C$	150
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.36	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ C$

*Drain current limited by maximum junction temperature

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	-	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^{note3}	$V_{GS} = 10V, I_D = 30A$	-	2.5	3.0	m Ω
		$V_{GS} = 4.5V, I_D = 15A$	-	4.2	6.0	
g_{FS}	Forward Transconductance	$V_{DS} = 5V, I_D = 10A$	-	48	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0MHz$	-	3400	-	pF
C_{oss}	Output Capacitance		-	356	-	pF
C_{rSS}	Reverse Transfer Capacitance		-	308	-	pF
Q_g	Total Gate Charge	$V_{DS} = 15V, I_D = 30A,$ $V_{GS} = 10V$	-	70	-	nC
Q_{gs}	Gate-Source Charge		-	12	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	16.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 15V, R_{GEN} = 1.8\Omega,$ $V_{GS} = 4.5V, I_D = 60A$	-	11	-	ns
t_r	Turn-On Rise Time		-	120	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	25	-	ns
t_f	Turn-Off Fall Time		-	60	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	150	-	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	400	-	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 20A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$V_{GS} = 0V, I_S = 60A,$ $di/dt = 100A/\mu s$	-	56	-	ns
Q_{rr}	Body Diode Reverse Recovery Time Charge		-	110	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : $T_C = 25^\circ\text{C}, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$
3. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

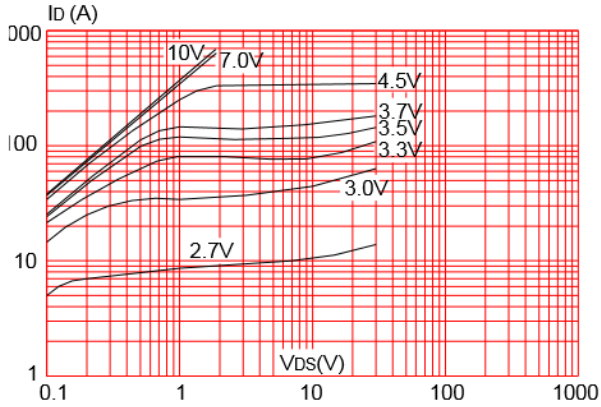


Figure 1. Output Characteristics

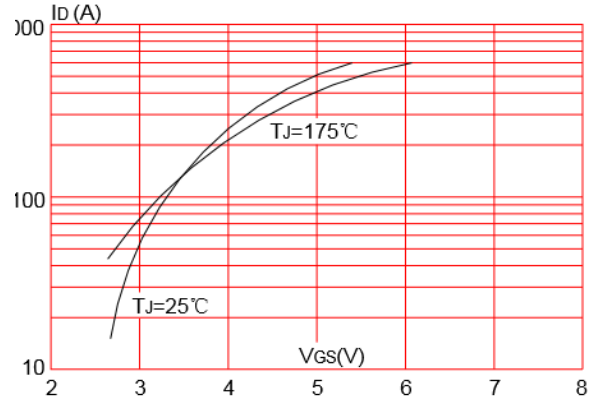


Figure 2. Transfer Characteristics

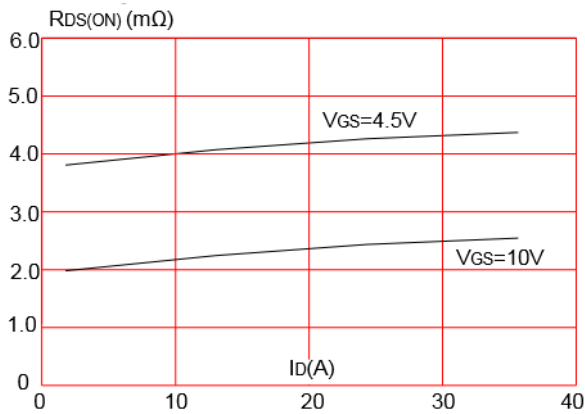


Figure 3. Drain-to-Source On Resistance

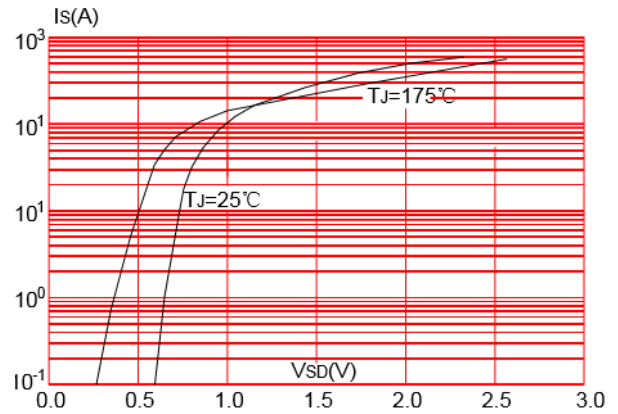


Figure 4. Body Diode Characteristics

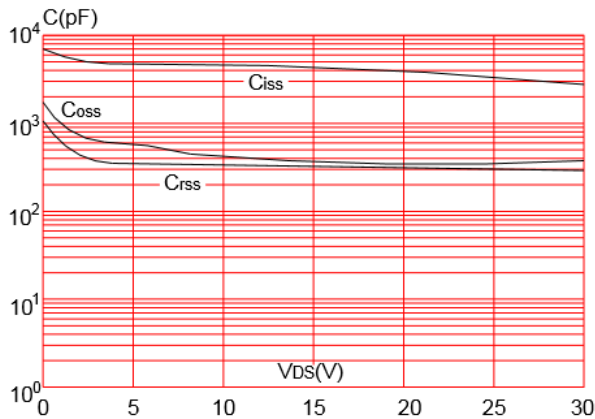


Figure 5. Capacitance Characteristics

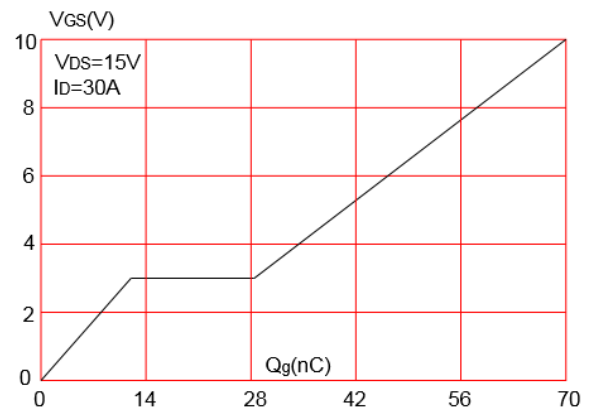


Figure 6. Gate Charge Characteristics

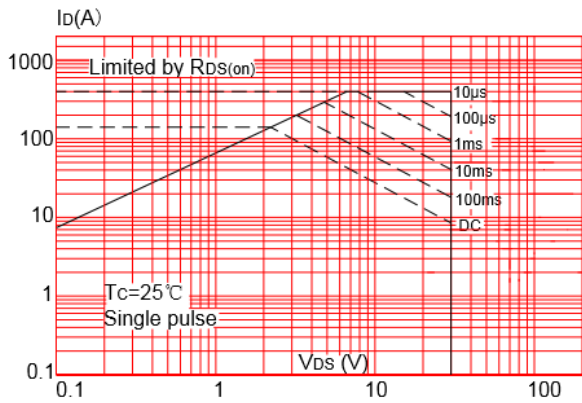


Figure 7. Maximum Safe Operating Area

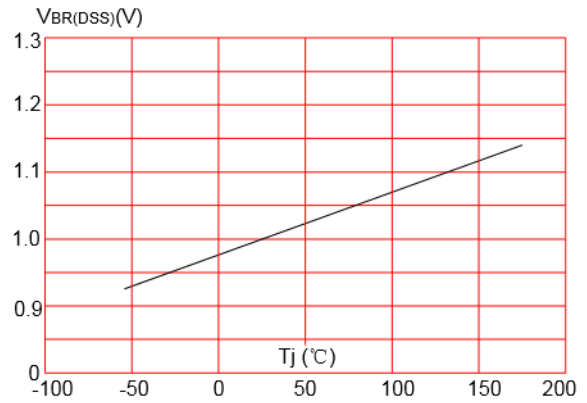


Figure 8. Normalized Breakdown Voltage VS. Junction Temperature

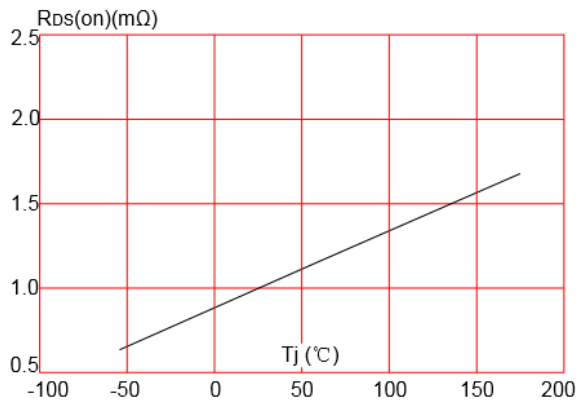


Figure 9. Normalized on Resistance VS. Junction Temperature

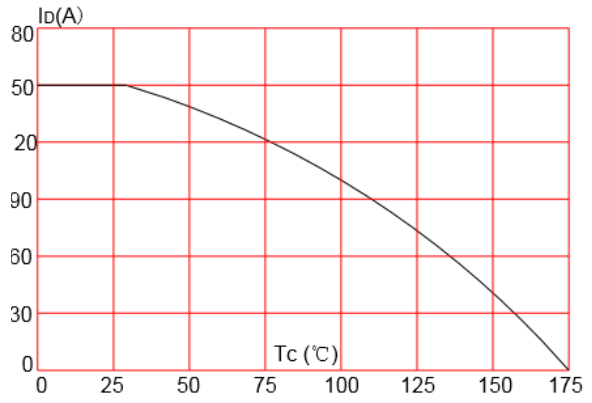


Figure 10. Maximum Continuous Drain Current VS. Case Temperature

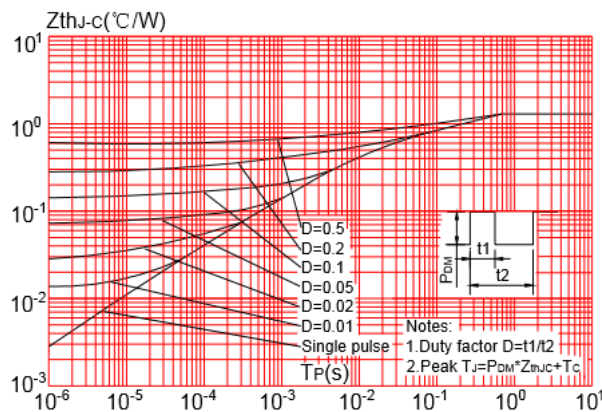


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

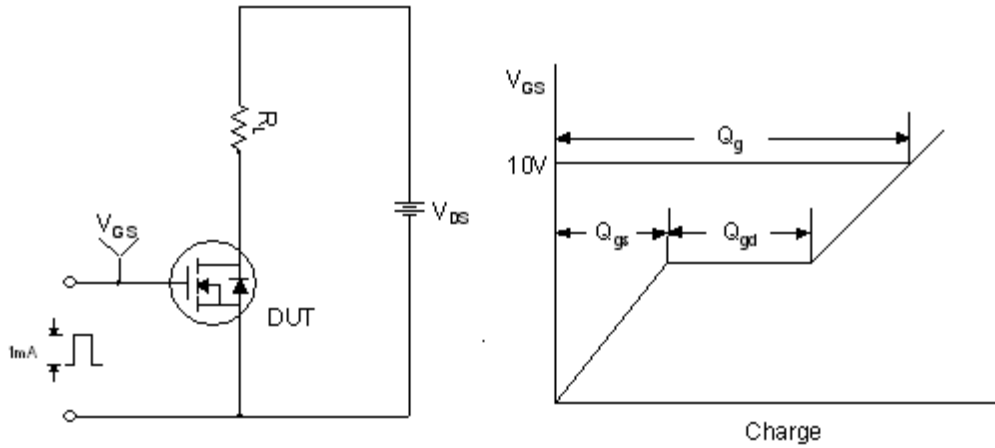


Figure 12. Gate Charge Test Circuit & Waveform

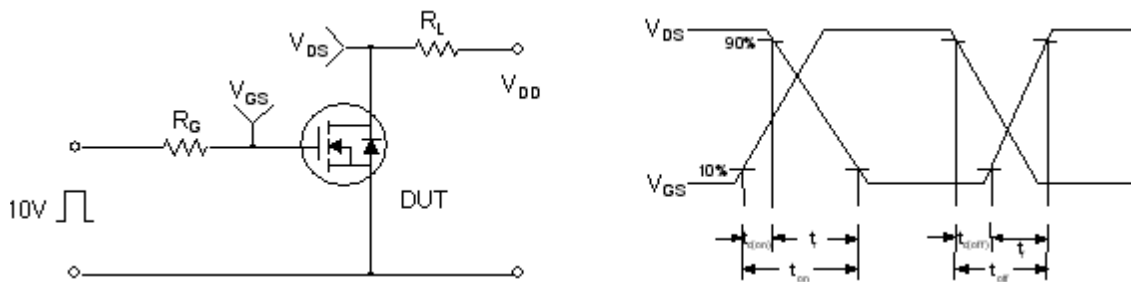


Figure 13. Resistive Switching Test Circuit & Waveforms

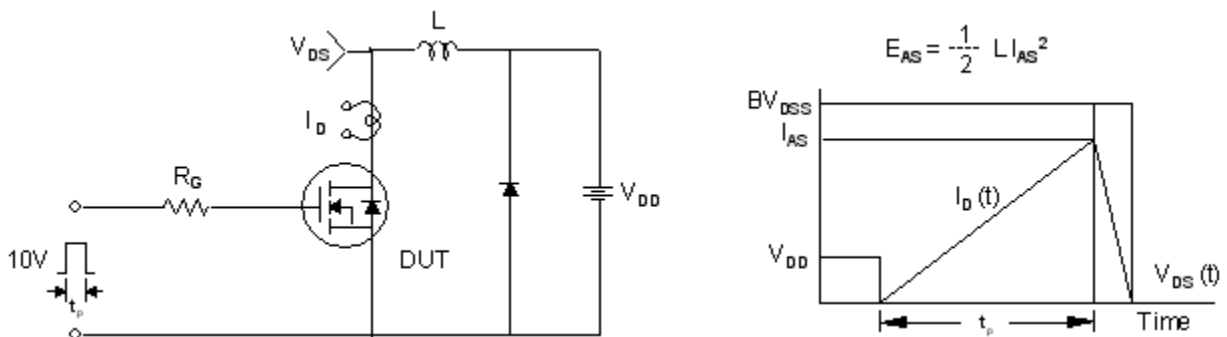


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

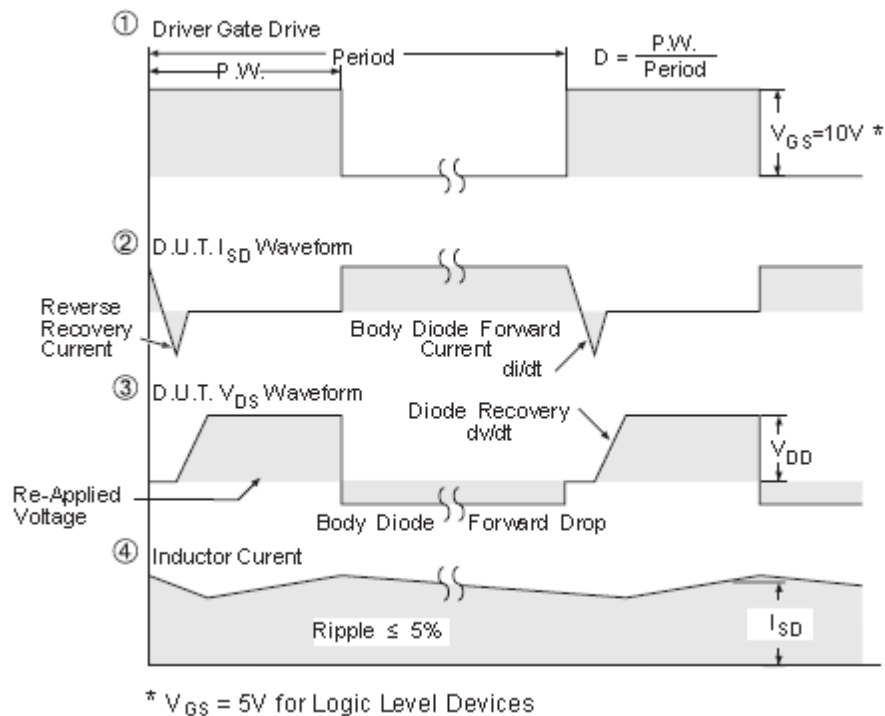
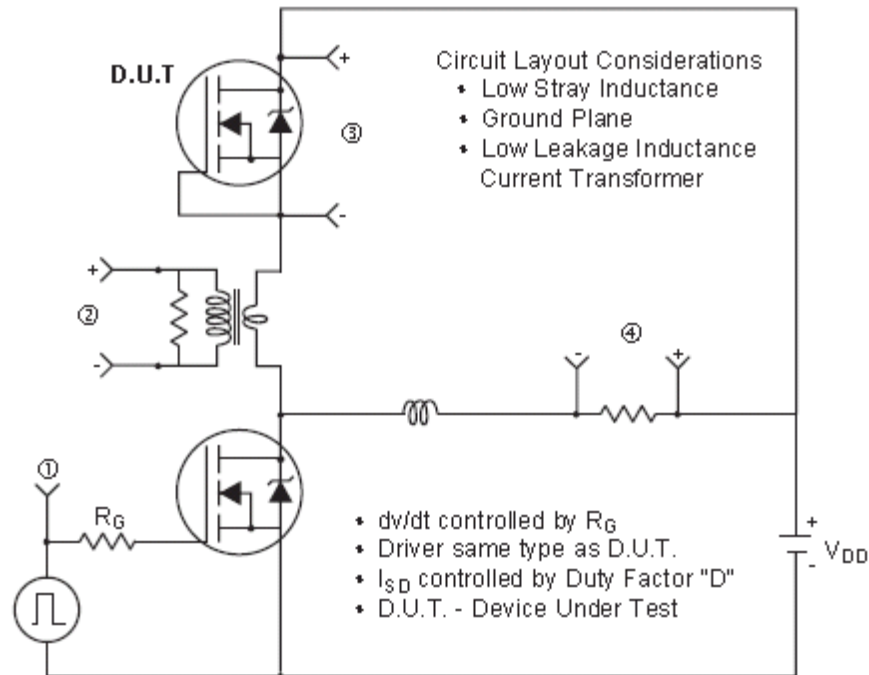
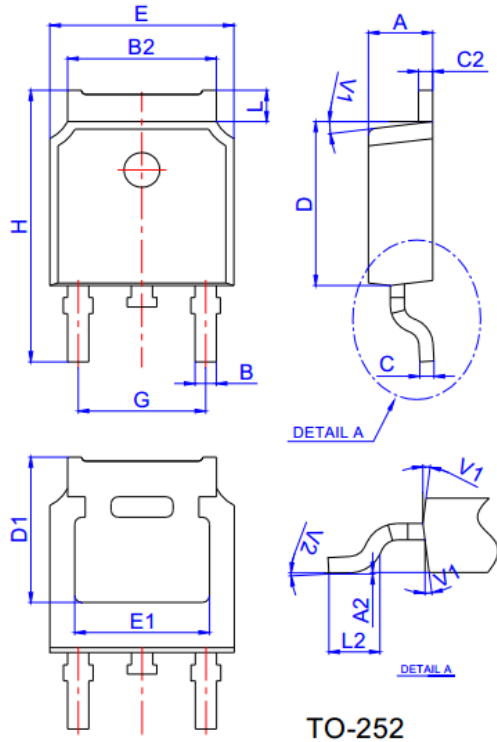


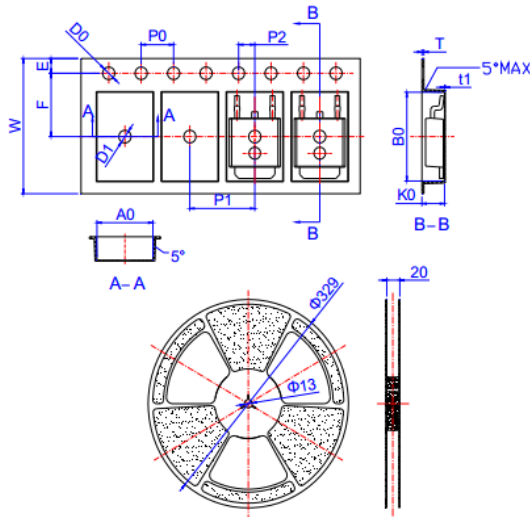
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TAPING	2,500	25,000	13inch

SFD160N03AT Product Description

Silicon N-Channel MOSFET



NOTE:

1. We strongly recommend customers check carefully on the trademark when buying our product, if there is any question, please don't be hesitate to contact us.
2. Please do not exceed the absolute maximum ratings of the device when circuit designing.
3. Winsemi Microelectronics Co., Ltd reserved the right to make changes in this specification sheet and is subject to change without prior notice.

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